

**AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions and listings of claims in the application.

**LISTING OF CLAIMS**

1. (Currently Amended) A semiconductor polishing composition comprising:  
fumed silica as abrasive grains, the fumed silica having a bulk density of 50 g/L or more and less than 100 g/L;  
an acidic aqueous solution;  
an alkali aqueous solution; and  
coarse particles of approximately 0.5 µm in diameter, the number of course particles being less no more than 140,000/0.5 ml, wherein the alkali aqueous solution contains at least one additive selected from a polishing accelerator, an oxidant, an organic acid, a complexing agent, a corrosion inhibitor and a surfactant.
2. (Original) The semiconductor polishing composition of claim 1, wherein a content of the fumed silica is in a range of 10% by weight to 30% by weight based on a total amount of the composition.
- 3.-6. (Cancelled)
7. (Previously Presented) The semiconductor polishing composition of claim 1, wherein the alkali aqueous solution includes at least one hydroxide selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

8. (Cancelled)

9. (Previously Presented) The semiconductor polishing composition of claim 2, wherein the alkali aqueous solution includes at least one hydroxide selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

10.-11. (Cancelled)